Product data sheet

1. General description

Ultrafast power diode in a SOD113 (TO-220F) plastic package.

2. Features and benefits

- · Low on-state loss
- Ultra low leakage
- Low switching loss
- Fast switching
- Soft recovery characteristic
- · High thermal cycling performance
- Low thermal resistance

3. Applications

- Home appliance power supply
- Discontinuous Current Mode (DCM) Power Factor Correction (PFC)

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_R	reverse voltage	DC	-	-	600	V
I _{F(AV)}	average forward current	δ = 0.5 ; T _h \leq 71 °C; square-wave; Fig. 1; Fig. 2; Fig. 3	-	-	15	А
I _{FRM}	repetitive peak forward current	δ = 0.5 ; t_p = 25 µs; $T_h \le 71$ °C; square-wave	-	-	30	Α
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sinusoidal waveform; Fig. 4	-	-	150	А
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sinusoidal waveform	-	-	165	А
Static charact	eristics					
V _F	forward voltage	I _F = 15 A; T _j = 25 °C; <u>Fig. 6</u>	-	1.1	1.38	V
		I _F = 15 A; T _j = 125 °C; <u>Fig. 6</u>	-	0.96	1.25	V
Dynamic char	acteristics					
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	50	60	ns

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode	mb	K — A
2	Α	anode		001aaa020
mb	n.c.	mounting base; isolated	TO-220F (SOD113)	

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BYT79X-600P	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 2-lead TO-220 "full pack"	SOD113

7. Marking

Table 4. Marking codes

Type number	Marking code
BYT79X-600P	BYT79X-600P

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{RRM}	repetitive peak reverse voltage		-	600	V
V_{RWM}	crest working reverse voltage		-	600	V
V_R	reverse voltage	DC	-	600	V
I _{F(AV)}	average forward current	δ = 0.5 ; T _h ≤ 71 °C; square-wave; <u>Fig. 1</u> ; <u>Fig. 2</u> ; <u>Fig. 3</u>	-	15	А
I _{FRM}	repetitive peak forward current	δ = 0.5 ; t _p = 25 µs; T _h ≤ 71 °C; squarewave	-	30	А
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sinusoidal waveform; Fig. 4	-	150	А
		t _p = 8.3 ms; T _{j(init)} = 25 °C; sinusoidal waveform	-	165	А
T _{stg}	storage temperature		-65	175	°C
T _j	junction temperature		-	175	°C

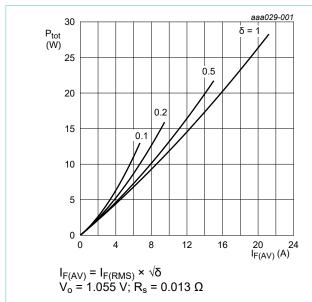


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values

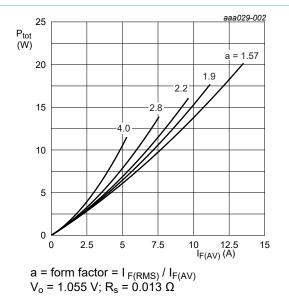


Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

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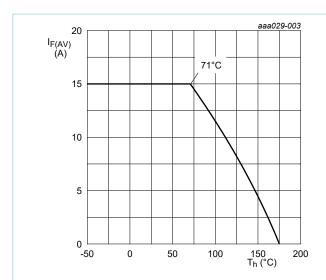


Fig. 3. Forward current as a function of heatsink temperature; maximum values

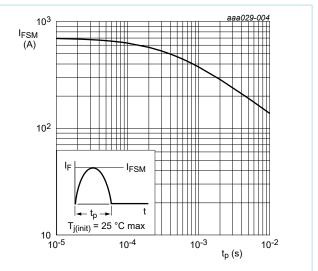
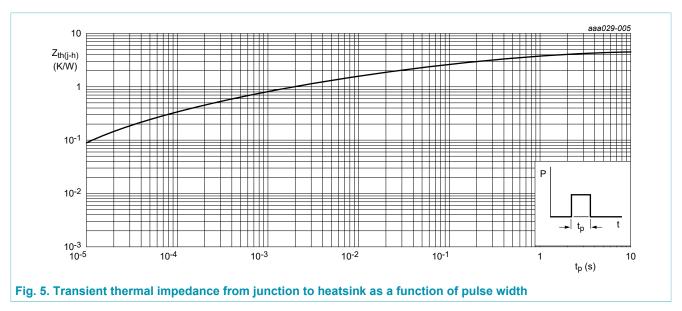


Fig. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-h)}	thermal resistance from junction to heatsink	with heatsink compound; Fig. 5	-	-	4.8	K/W
R _{th(j-a)}	thermal resistance from junction to ambient free air	in free air	-	55	-	K/W



10. Isolation characteristics

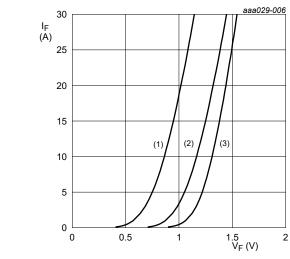
Table 7. Isolation characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{isol(RMS)}	RMS isolation voltage	50 Hz ≤ f ≤ 60 Hz; RH ≤ 65 %; from all pins to external heatsink; sinusoidal waveform; clean and dust free	-	-	2500	V
C _{isol}	isolation capacitance	from cathode to external heatsink	-	10	-	pF

11. Characteristics

Table 8. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V _F	forward voltage	I _F = 15 A; T _j = 25 °C; <u>Fig. 6</u>	-	1.1	1.38	V
		I _F = 15 A; T _j = 125 °C; <u>Fig. 6</u>	-	0.96	1.25	V
I _R	reverse current	V _R = 600 V; T _j = 25 °C	-	1	10	μA
		V _R = 600 V; T _j = 125 °C	-	80	200	μA
Dynamic ch	naracteristics					
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	50	60	ns
I _{RM}	peak reverse recovery current	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A/}\mu\text{s};$ $T_j = 100 \text{ °C}$	-	3	-	Α
Q _r	recovered charge	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	60	-	nC
		$I_F = 2 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 20 \text{ A/}\mu\text{s};$ $T_i = 25 \text{ °C}; Fig. 7$	-	60	110	nC



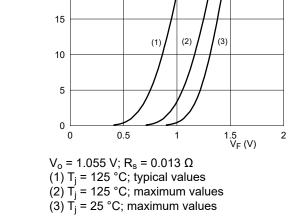


Fig. 6. Forward current as a function of forward voltage

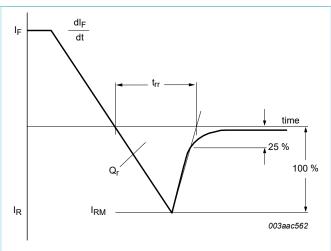
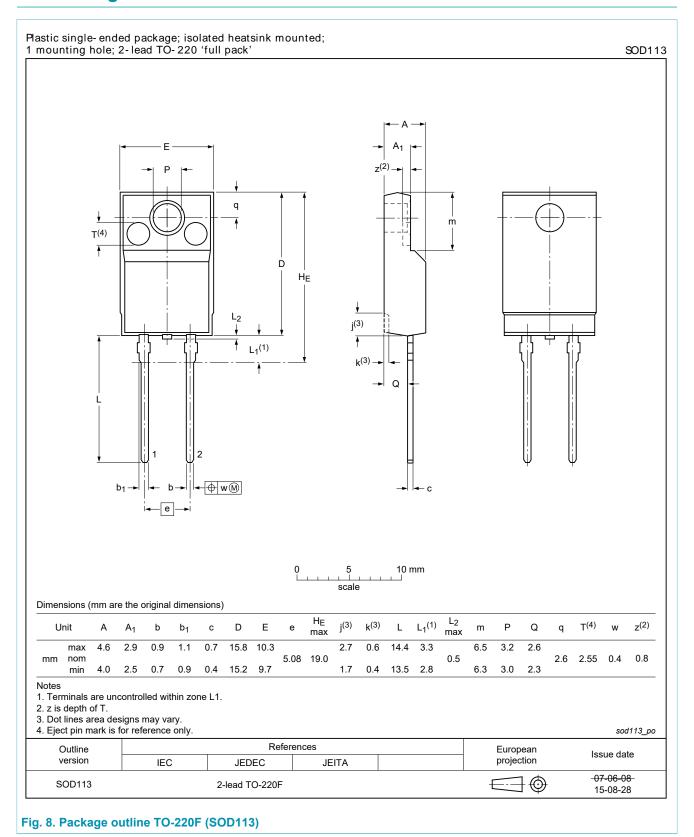


Fig. 7. Reverse recovery definitions; ramp recovery

12. Package outline



13. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions".
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